H.T	No:			R1	8	Course Code: A30	006
CA	TOTAKERI		(UGC	AUTONOM	(OUS)	CHNOLOGY	
Cou	B.Tech III irse Name: N	I Semester UMERIC	r Regular & S CAL METH(ODS & CO	ry Examinat MPLEX VA	ions Feb/March -2023 RIABLES	
D-4	. 20 02 2023 4	N		on for EEE Time: 3 hour		Max.Mai	·ks: 70
Date	e: 20.02.2023 A		Note: Assume				1131 70
			Answer all TE Each questio			y) 10x2	2=20M
1. Fin	d the Laplace t	ransform o	of e ^t Sin(t).				2 M
	nd the inverse L			unction $F(s)$	$=\frac{1}{a(a+1)}$.		2 M
3. If					,	then find x_2 by Regula	2 M
	ate the Gauss fo	orward inte	rpolation form	ula.			2 M
5. If	$\frac{dy}{dx} = -y, y(0) =$	1, $h = 0.01$	then applying	g Euler's met	hod, compute	the value of y_1	2 M
6. Sta	State the formula for Simpson's 3/8 th rule.						
7. Fir	nd where the fu	nction (i)	$w = \frac{1}{z}(ii)\frac{z}{z-1}$	fails to be an	alytic.		2 M
8. Fin	nd the value of	K so thet	$x^2 + 2x + ky^2$	may be harr	nonic.		2 M
9. Ob	otain the Taylor	s series ex	pansion of $\frac{1}{7}$	$\frac{1}{1}$ in $ Z =2$			2 M
10. Fin	nd the poles of	$(z-1)^2$					2 M
		$z(z-2)^{-}$					
An	swer the follow	ving. Each	question car	PART-B ries TEN Ma	arks.	5x1	0=50M
11.A).	Find the Lapl	ace transfo	orm of $te^{2t} \sin 3t$	ßt.			10M
				OR			
11. B).	Applying Lap $(D^2 + 9)y = s$		forms Solve th $1, y^1(0) = 0$	e differential	equation.		10M
12. A).	Find the root Newton-Rapl			e interval [0,	1] correct up	to two decimal places l	oy 10M
12. B).	Using Newton's forward formula, find the value of f(1.6) if						
	v	1.4	1.8	2.2	2.6	3	
	Y	4.82	5.96	6.5	7.2	8.4	

1.

2.

3.

4.

5.

7.

10M

X	10	20	30	40	50	60	70	80
d(x)	4	7	9	12	15	14	8	3

OR

13. B). Using R-K method, find y(0.2) for the equation dy/dx=y-x, y(0)=1,take h=0.1. given that y=1 when x=0

14. A). Show that the function $f(z) = \sqrt{|xy|}$ is not analytic at the origin, although Cauchy-Riemann equations are satisfied at that point.

OR

14. B). Prove that $u = x^2-y^2-2xy-2x+3y$ is harmonic. Find f(z)=u+iv By using Milne-Thomson 10M method.

15. A). Evaluate $\int_{c} \frac{z^3}{(z-1)^2(z-3)} dz$ where c is |Z|=2 by Residue theorem.

OR

15. B). Evaluate $\int_{c} \frac{z-3}{(z^2+2z+5)}$ where C is the circle
(i) |Z|=1, (ii) |Z+1-i|=2



(UGC AUTONOMOUS)

B.Tech III Semester Regular & Supplementary Examinations Feb/March-2023 Course Name: ELECTRICAL ENGINEERING

(Electronics & Communication Engineering)

Date: 22.02.2023 AN Time: 3 hours Max.Marks: 70

(Note: Assume suitable data if necessary)

PART-A

Answer all TEN questions (Compulsory)

Each question carries TWO marks. 10x2=20M

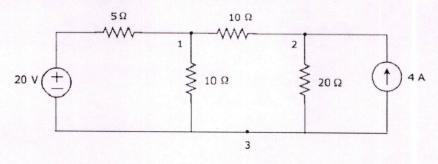
- 1. State Kirchhoff's laws.
- 2. Three equal Resistors of 10hm are connected in series and parallel to 6V source calculate the 2 M total current in both cases.
- 3. Define RMS and Average Value of a sinusoidal waveform.
- 4. Define Q factor and bandwidth.
- 5. List four properties of Laplace transform. 2 M
- 6. Determine the poles and zeros of the driving point impedance $Z(s) = \frac{s+2}{s(s-1)}$ 2 M
- 7. Define Efficiency and regulation of a Transformer. 2 M
- 8. List the differences between ideal and practical transformers.
- 9. List the importance of brushes and slip rings in DC machine.
- 10. Define slip and slip speed.

PART-B Answer the following. Each question carries TEN Marks.

5x10=50M

11.A). Calculate the Nodal Voltage in the circuit shown below

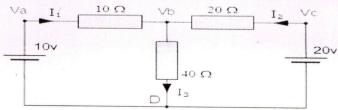
10M



OR

11. B). Apply super position theorem to calculate the current I3 in the network shown below

10M



(P.T.O..)

12. A). A sinusoidal voltage of $V(t)=200\sin(314t+30^{\circ})$ Volts has applied to a 10 ohms resistor, 10M calculate the following i) Maximum voltage, ii) Frequency, iii) Form factor, iv) Current and v) Power factor. OR A series RLC circuit under resonance contains R=1ohm, L=1mH and C=1pF connected to 10M 12. B). a function generator of 10V, calculate the following i) Resonance frequency, ii) Quality factor, iii) bandwidth and iv) half power frequencies. 13. A). Derive the expression for the current in a series RL circuit excited by a DC voltage source 10M at t=0 sec. Calculate the Time constant and final value for R=1ohm & L=1mh. OR 13. B). Derive the following Two port parameters for the circuit shown below i) Impedance 10M parameters, ii) admittance parameters 5Ω 12 Ω ≶8Ω 14. A). Elaborate the procedure to obtain Losses in the Transformer by conducting suitable tests. 10M 14. B). Explain the operation and working principle of transformer. 10M 10M 15. A). Derive the EMF and Torque equation of a DC machine.

10M

15. B). Explain the operating principle of Induction motor.

H.T No: **R18** Course Code: A30402 NOE CMR COLLEGE OF ENGINEERING & TECHNOLOGY CMR (UGC AUTONOMOUS) B.Tech III Semester Regular & Supplementary Examinations Feb/March-2023 Course Name: PROBABILITY & STOCHASTIC PROCESSES (Electronics & Communication Engineering) Date: 24.02.2023 AN Time: 3 hours Max.Marks: 70 (Note: Assume suitable data if necessary) PART-A Answer all TEN questions (Compulsory) Each question carries TWO marks. 10x2 = 20MState the fundamental Axioms of probability. 2 M List the various conditions that events A, B and C must satisfy if they are to be statistically 2 M independent. If the density function of a random variable X is $f_X(x) = x/2$ $0 \le x \le 2$, find $P\{x > 1.5/x > 1\}$. 2 M State the properties of distribution function. 2 M State Central Limit Theorem. 2 M Show that var(X+Y) = var(x)+var(Y), if X&Y are independent random variables. 2 M Define a random process, when does it represent a random variable? 2 M Contrast between auto correlation and cross correlation functions. 2 M Relate Auto correlation function and power density spectrum. 2 M State the properties of Cross power density spectrum. 2 M PART-B Answer the following. Each question carries TEN Marks. 5x10=50Mi) An experiment consists of observing the sum of the outcomes when two fair dice are thrown. 11.A). 5M Find the probability that the sum is 7 and find the probability that the sum is greater than 10. 5M ii) Three students A, B, C are given a problem. The probabilities of their solving the problem are 3/4, 2/3 and 1/4 respectively. Find the probability that the problem is solved if all of them try it. OR A Random Variable 'X' has Rayleigh distribution. Define its density function. Find 10M

11. B).

Cumulative Distribution Function (F_X(x)), Mean, Mean square value and Variance.

i) State and Prove Total Probability Theorem.

2.

3.

4.

5.

6.

7.

8.

9.

5M

ii) For a certain binary communication channel, the probability that a transmitted '0' is received as a '0' is 0.8 and the probability that a transmitted '1' is received as '1' is 0.9. If the probability that a '0' is transmitted is 0.4, find the probability that a) a '1' is received

5M

b) a '1' was transmitted given that a '1' was received.

12. B). Derive the Poisson density function and find its mean & variance.

10M

- 13. A). i) Find the joint characteristic function and moment generating function of uniformly distributed RV 'X' over the interval (-1,+1).
- 5M
- ii) If X and Y are independent exponentially distributed random variables with probability density functions e^{-x} , $x \ge 0$ and e^{-y} $y \ge 0$ respectively. Find the joint density function of Z = X + Y.

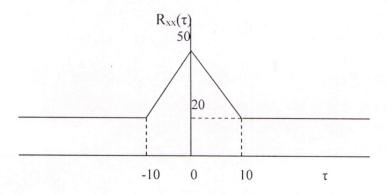
5M

OR

13. B). State any three properties of joint characteristic function. Let Z=X+Y-C, where X and Y are independent random variables with variance σ^2_X , σ^2_Y and C is constant. Find the variance of Z in terms of σ^2_X , σ^2_Y and C. 10M

14. A). For a stationary ergodic process having the autocorrelation function shown in fig. Find i) E[X(t)] (ii) $E[X^2(t)]$ (iii) σ_x^2

10M



OR

- 14. B). Show that the random process $X(t) = A \cos(\omega_0 t + \theta)$ is Wide Sense Stationary (WSS), if A and ω_0 are constants and θ is uniformly distributed Random variable in the interval $(0,2\pi)$.
- 15. A). A product device is applied with two inputs, one is a random signal X(t) and the other is a high frequency carrier A $Cos(\omega_0 t)$. Find the power spectrum of response in terms of power spectrum of input X(t).

10M

OR

15. B). Derive the relationship between cross power density and cross correlation function.

10M



(UGC AUTONOMOUS)

B.Tech III Semester Regular & Supplementary Examinations Feb/March-2023 Course Name: SWITCHING THEORY & LOGIC DESIGN

Dat	e: 27.02.2023 AN	ronics & Communication Engineering) Time: 3 hours Max.Marks	: 70
<u> </u>		Note: Assume suitable data if necessary)	
		PART-A	
	A	Answer all TEN questions (Compulsory) Each question carries TWO marks. 10x2=	2014
		Each question carries 1 WO marks.	201VI
. Gi	ven that $(64)_{10} = (100)_b$, de	etermine the value of b.	2 M
. Ob	tain the Dual of the follow	ring Boolean expressions	2 N
	A+B+A'B'C ate the types of ROM.	(ii) AB+A (B+C) +B' (B+D)	2 M
Im	plement OR gate using on	ly two input NAND gates.	2 N
De	fine race around condition		2 M
W	rite the characteristic equat	ion for JK Flip-flop.	2 M
Lis	st out the applications of sh	nift registers and counters.	2 N
	sume that the 5bit binary of 4 input pulses.	counter starts in the 0000 state then what will be the count after	2 M
Co	ompare mealy and Moore n	nodel of finite state machine.	2 M
0. W	hat is state reduction and w	hat is the need for state reduction.	2 N
		PART-B	
Ans	swer the following. Each	question carries TEN Marks. 5x10=	50M
1.A).	Simplify the following Bo (i) $F = (A+B)(A'+C)(B+C)$	[2012] [10M
1. B).	Convert the given decin BCD equivalent.	nal number 234 to binary, quaternary, octal, hexadecimal and	10N
2. A).	Simplify the following $F(a, b, c, d) = \sum m(0,4,8,10)$	expression to sum of products using Tabulation Method: ,12,13,15) +d(1,2)	10N
		OR	
2. B).	Explain Carry Look Ahea	nd Adder circuit with the help of logic diagram.	10N
3. A).	flip flop.	l, characteristics table and derive characteristics equation of JK	5N
	ii) Design T Flip Flop by	using JK Flip Flop and draw the timing diagram	5N
		OR	
3. B).	i) Construct a JK flip-flopii) Convert SR flip – flop	using D flip-flop, 2×1 multiplexer and an inverter. to T flip – flop.	5N 5N
		(P.T.O)	

14. A). Describe the operation of four bit synchronous binary counter with neat sketch.

OR

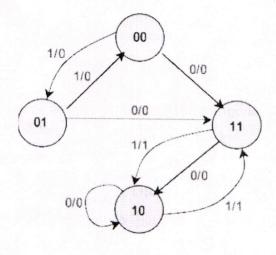
14. B). With a neat circuit diagram and function table, explain the logical operation of a 4-bit universal shift register in detail.

15. A). Draw the ASM chart for binary multiplier.

OR

15. B). A finite state machine (FSM) with input X and output Z is described by the state diagram showing below
i) Obtain the corresponding state transition table

ii) Design the FSM with D flip-flops and gates



R18 Course Code: A30401 H.T No:



CMR COLLEGE OF ENGINEERING & TECHNOLOGY

(UGC AUTONOMOUS)

Co	B.Tech III Semester Regular & Supplementary Examinations Feb/March-2023 ourse Name: ELECTRONIC DEVICES & CIRCUITS	
Co	(Common for EEE & ECE)	
Da	ite: 01.03.2023 AN Time: 3 hours Max.Man	ks: 70
	(Note: Assume suitable data if necessary) PART-A Answer all TEN questions (Compulsory) Each question carries TWO marks.	2=20M
	Each question carries 1 wo marks.	2-201VI
1. W	Vrite the effect of temperature on diode characteristics.	2 M
2. D	Define the operating principle of Photo diode. Write two of its applications.	2 M
3. D	Define and why is peak inverse voltage important?	2 M
4. W	Vrite different types of filters and mention its purpose.	2 M
5. E	explain the base width modulation in BJT.	2 M
6. W	Which of the BJT configurations are suitable for impedance matching applications. Why?	2 M
7. E	Explain the DC and AC load Line analysis.	2 M
8. D	Describe the thermal runaway, why does it occur.	2 M
	for a p-channel Silicon FET, with effective width 'a'= $2X10^{-4}$ cm and channel resistivity =10 Ω . Solve for the pinch off voltage.	y 2 M
	lot drain and transfer characteristic of JFET.	2 M
Aı	PART-B nswer the following. Each question carries TEN Marks. 5x1	0=50M
<u>A</u>	iswer the following. Each question earries TETV Marks.	0 00111
11.A).	i) Illustrate the current components of a PN Junction diode and derive the diode current equation.	nt 6M
	ii) Explain the static characteristics of SCR. Mention SCR applications.	4M
	OR	
11. B).	 i) Define tunneling phenomena and explain the V-I characteristics of a Tunnel diode wit the help of energy band diagrams and list its applications. 	h 6M
	ii) Zener diode can be used as a voltage regulator. Justify it.	4M
12. A).	. i) Explain and derive the expressions for average DC current, RMS value of current, D Power output and AC Power input for a Full wave rectifier. List the advantages.	C 6M
	ii) A full-wave single phase rectifier employs a pi- section filter consisting of two 4 μ capacitances and a 20 H choke. The transformer voltage to the center tap is 300 V rm The load current is 500 mA. Measure the dc output voltage and the ripple voltage. The resistance of the choke is 200 Ω	S.
	OR	
12. B).		nd 4M
	ii) Demonstrate the working principle of C filter with a circuit diagram and derive the expression for its ripple factor. List the advantages and disadvantages.	ne 6M

13. A).	i) Define three regions of BJT operation. Explain the operation of an NPN transistor.ii) Explain neatly the CB configuration of BJT transistor along with its VI characteristics.	4M 6M
	OR	
13. B).	i) Discuss, how the h-parameters are determined from transistor Characteristics.	6M
	ii) With a diagram, describe how BJT transistor acts as an amplifier.	4M
14. A).	i) Explain Collector to Base bias of a transistor with a circuit diagram and determine Q-point.	6M
	ii) For the circuit shown in Figure, $\beta = 100$ for the silicon transistor. Calculate V_{CE} and I_{C}	4M
	$R_1 = 10 \text{ k}\Omega$ $R_C = 1 \text{ k}\Omega$	
	V ₁ • · · · · · · · · · · · · · · · · · ·	
	C_1 C_2 C_1 C_2 C_2 C_1 C_2	
	OR	
14. B).	i) Draw the circuit diagram of voltage divider bias of a Transistor and determine its Q-point.	6M 4M
	ii) Explain diode compensation technique for the parameters of V_{BE} and I_{CO} .	
15. A).	i) Write the construction, operation and characteristic behavior of JFET under various biasing conditions.	4M
	ii) Draw the circuit diagram of Common Source amplifier with voltage divider bias and compare BJT transistor with FET.	6M
	OR	
15. B).	i) Describe the operation of common drain FET amplifier and derive the equation for	CM

4M

ii) Explain the operation of Enhancement mode MOSFET in detail.

voltage gain.





	B.Tech III Semester Regular & Supplementary Examinations Feb/March-2023 Course Name: PYTHON PROGRAMMING	
	(Common for CE, EEE, ME, ECE, CSE, IT, CSC & CSM) Date: 03.03.2023 AN Time: 3 hours Max.Ma	rks: 70
	(Note: Assume suitable data if necessary) PART-A	
	Answer all TEN questions (Compulsory) Each question carries TWO marks. 10x	2=20M
1.	Mention any two features of Python.	2 M
2.	What is implicit conversion? Give an example.	2 M
3.	Python strings are immutable. Justify.	2 M
4.	Do Loop statements have else clause? When will it be executed?	2 M
5.	How will you update list items? Give one example.	2 M
6.	What is difference between list and tuple in python?	2 M
7.	Explain what a constructor does.	2 M
8.	How is the lifetime of an object determined? What happens to an object when it dies?	2 M
9.	Explain what happens when a program receives a non-numeric string when a number is expected as input.	s 2 M
10.	When would you make a data field read-only, and how would you do this?	2 M
	PART-B	
	Answer the following. Each question carries TEN Marks. 5x1	0=50M
11.4	A). Write Python Program to reverse a number and also find the Sum of digits in the reverse number. Prompt the user for input.	ed 10M
	OR	
11.	B). Explain the basic data types available in Python with examples.	10M
12.	A). Write a function to determine whether a given natural number is a perfect number. natural number is said to be a perfect number if it is the sum of its divisors. OR	A 10M
12.	그 아니는 그 그 그 그 그 아이를 가장 하는 것이 되었습니다. 그는 그는 그는 그는 그는 그를 가장 하는 것이 되었습니다. 그는 그는 그를 가장 하는 것이 없는 것이다. 그는 그를 가장 하는 것이다.	10M
13.	least 3). If the given string already ends with 'ing' then add 'ly'. instead. If the string	
	length of the given string is less than 3, leave it unchanged. OR	

13. B). Compare and contrast different functions and methods used in dictionaries and set.

10M

14. A).	i) Write a short notes on different built in attributes associated with a class.	5M
	ii) With the help of examples explain the concept of class methods and static methods.	5M
	OR	
14. B).	Write a program that uses datetime module within a class. Enter manufacturing date and expiry date of the product. The program must display the years, months, and days that are left for expiry.	10M
15. A).	Write a line of code that adds a Float Field to a window, at position (1, 1) in the grid, with an initial value of 0.0, a width of 15, and a precision of 2.	10M
	OR	
15. B).	Describe the Graphical user interface using the tkinter module and widgets.	10M



(UGC AUTONOMOUS)

B. Tech III Semester Supplementary Examinations Feb/March-2023

	B.Tech III Semester Supplementary Examinations Feb/March-2023 Course Name: JAVA PROGRAMMING						
			(Common for EEE & ECE)				
	Dat	e: 03.03.2023 AN		x.Marks: 70			
			(Note: Assume suitable data if necessary) PART-A Answer all TEN questions (Compulsory) Each question carries TWO marks.	10x2=20M			
1.	Wł	nat is the purpose of JVN	M?	2 M			
2.		nat are the integer data to		2 M			
3.		nat are the uses of final l		2 M			
4.		ferentiate abstract class	(1) 1 전에 보고 있는 사람들은 1 전에 보고 있는 1 전에 보고 있는 1 전에 보고 있는 1 전에 보고 있다.	2 M			
5.	Ex	plain briefly about wrap	oper classes in Java.	2 M			
6.	Lis	t the differences betwee	en throw and throws keyword.	2 M			
7.	Wł	nat are the different way	s to create threads in Java?	2 M			
8.	De	fine thread.		2 M			
9.	Exp	plain briefly about seria	lization in Java.	2 M			
10.	. Wh	nat is the purpose of Sca	nner class?	2 M			
			PART-B				
	Ans	wer the following. Eac	th question carries TEN Marks.	5x10=50M			
11	.A).	Explain the various typ	oes of constructors in Java with example program. OR	10M			
11.	. B).	i) Explain the concept of	of method overloading with a program.	5M			
		ii) Explain about classe	es and objects in Java.	5M			
12	. A).	i) Demonstrate comma	nd line arguments in Java with an example program.	5M			
			m to demonstrate the concept of interfaces.	5M			
			OR				
12	. B).	Explain the various wa	ys of declaring arrays in Java with an example program.	10M			
13	. A).	Write the differences b supported by StringBut	etween String and StringBuffer. Explain the various method ffer class.	s 10M			
			OR				
13	. B).	Write a Java program t	o demonstrate nested try statements.	10M			
14.	. A).	i) Explain the concept of	of multithreading in Java.	5M			
		ii) Explain the life cycl	e of a thread.	5M			
			OR				
14.	. B).	Write a multithreaded J	Java program by implementing Runnable interface.	10M			
15.	. A).	Explain the concept of	database connectivity in java.	10M			
			OR				
15.	. B).	Write a Java program t	o demonstrate the RandomAccessFile operations.	10M			